

Power MOSFET



P-Channel MOSFET

FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Surface-mount (IRFR9110, SiHFR9110)
- Straight lead (IRFU9110, SiHFU9110)
- Available in tape and reel
- P-channel
- Fast switching
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE
Available

PRODUCT SUMMARY

V_{DS} (V)	-100	
$R_{DS(on)}$ (Ω)	$V_{GS} = -10$ V	1.2
Q_g (Max.) (nC)	8.7	
Q_{gs} (nC)	2.2	
Q_{gd} (nC)	4.1	
Configuration	Single	

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The DPAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU, SiHFU Series) is for through-hole mounting applications. Power dissipation levels up to 1.5 W are possible in typical surface-mount applications.

ORDERING INFORMATION

Package	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	IPAK (TO-251)
Lead (Pb)-free and halogen-free	SiHFR9110-GE3	SiHFR9110TRL-GE3	SiHFR9110TR-GE3	IRFR9110TRPbF-BE3	SiHFU9110-GE3
Lead (Pb)-free	IRFR9110PbF	IRFR9110TRLPbF ^a	IRFR9110TRPbF ^a	IRFR9110TRRPbF	IRFU9110PbF

Note

- a. See device orientation

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	-100	V	
Gate-source voltage	V_{GS}	± 20		
Continuous drain current	I_D	V_{GS} at -10 V	$T_C = 25^\circ\text{C}$	A
			$T_C = 100^\circ\text{C}$	
Pulsed drain current ^a	I_{DM}	-12	W/ $^\circ\text{C}$	
Linear derating factor		0.20		
Linear derating factor (PCB mount) ^e		0.020		
Single pulse avalanche energy ^b	E_{AS}	140	mJ	
Repetitive avalanche current ^a	I_{AR}	-3.1	A	
Repetitive avalanche energy ^a	E_{AR}	2.5	mJ	
Maximum power dissipation	P_D	$T_C = 25^\circ\text{C}$	25	W
Maximum power dissipation (PCB mount) ^e		$T_A = 25^\circ\text{C}$	2.5	
Peak diode recovery dV/dt ^c	dV/dt	-5.5	V/ns	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$	
Soldering recommendations (peak temperature) ^d	For 10 s	260		

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
 b. $V_{DD} = -25$ V, starting $T_J = 25^\circ\text{C}$, $L = 21$ mH, $R_g = 25 \Omega$, $I_{AS} = -3.1$ A (see fig. 12)
 c. $I_{SD} \leq -4.0$ A, $di/dt \leq 75$ A/ μs , $V_{DD} \leq V_{DS}$, $T_J \leq 150^\circ\text{C}$
 d. 1.6 mm from case
 e. When mounted on 1" square PCB (FR-4 or G-10 material)



THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	-	110	°C/W
Maximum junction-to-ambient (PCB mount) ^a	R_{thJA}	-	-	50	
Maximum junction-to-case (drain)	R_{thJC}	-	-	5.0	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material)

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		- 100	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$		-	- 0.093	-	V/°C
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		- 2.0	-	- 4.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = - 100\text{ V}, V_{GS} = 0\text{ V}$		-	-	- 100	μA
		$V_{DS} = - 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	- 500	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = - 10\text{ V}$	$I_D = - 1.9\text{ A}^b$	-	-	1.2	Ω
Forward transconductance	g_{fs}	$V_{DS} = - 50\text{ V}, I_D = - 1.9\text{ A}$		0.97	-	-	S
Dynamic							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = - 25\text{ V},$ $f = 1.0\text{ MHz},$ see fig. 5		-	200	-	pF
Output capacitance	C_{oss}			-	94	-	
Reverse transfer capacitance	C_{riss}			-	18	-	
Total gate charge	Q_g	$V_{GS} = - 10\text{ V}$	$I_D = - 4.0\text{ A}, V_{DS} = - 80\text{ V},$ see fig. 6 and 13 ^b	-	-	8.7	nC
Gate-source charge	Q_{gs}			-	-	2.2	
Gate-drain charge	Q_{gd}			-	-	4.1	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = - 50\text{ V}, I_D = - 4.0\text{ A},$ $R_g = 24\text{ }\Omega, R_D = 11\text{ }\Omega,$ see fig. 10 ^b		-	10	-	ns
Rise time	t_r			-	27	-	
Turn-off delay time	$t_{d(off)}$			-	15	-	
Fall time	t_f			-	17	-	
Internal drain inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal source inductance	L_S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	- 3.1	A
Pulsed diode forward current ^a	I_{SM}			-	-	- 12	
Body diode voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = - 3.1\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	- 5.5	V
Body diode reverse recovery time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = - 4.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$		-	80	160	ns
Body diode reverse recovery charge	Q_{rr}			-	0.17	0.30	μC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\text{ }\%$



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

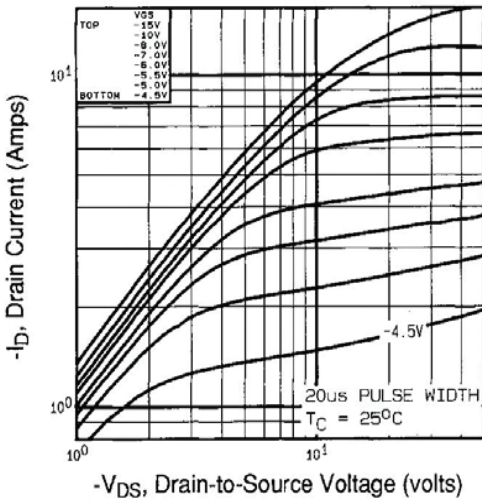


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

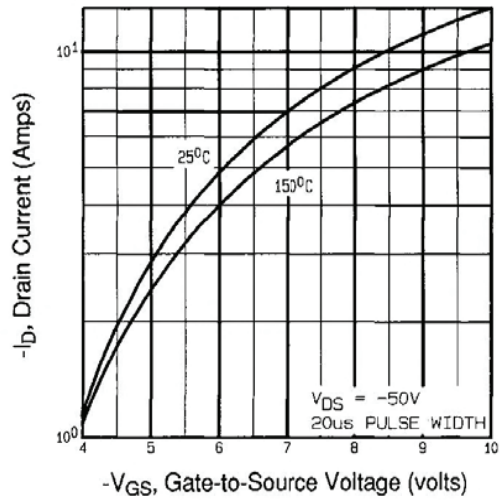


Fig. 2 - Typical Transfer Characteristics

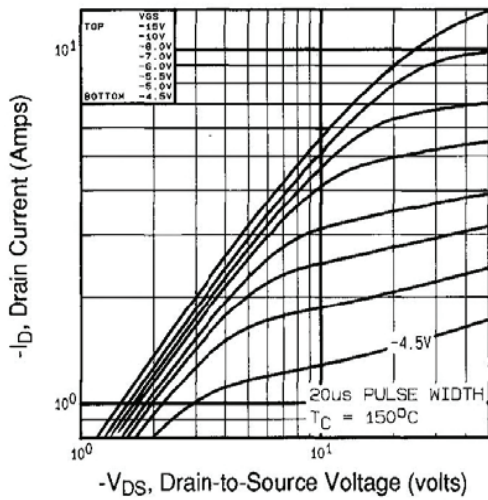


Fig. 1 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

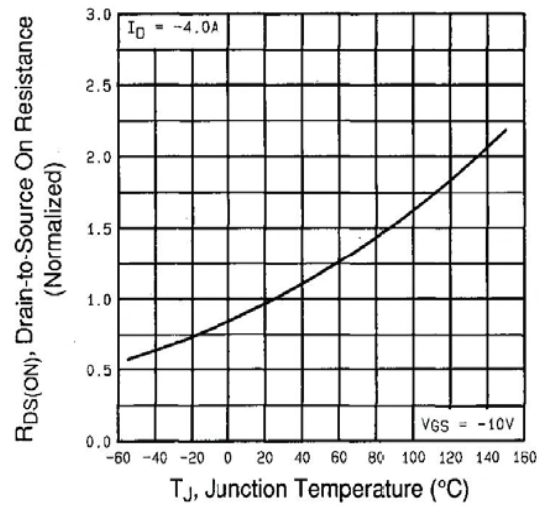


Fig. 3 - Normalized On-Resistance vs. Temperature

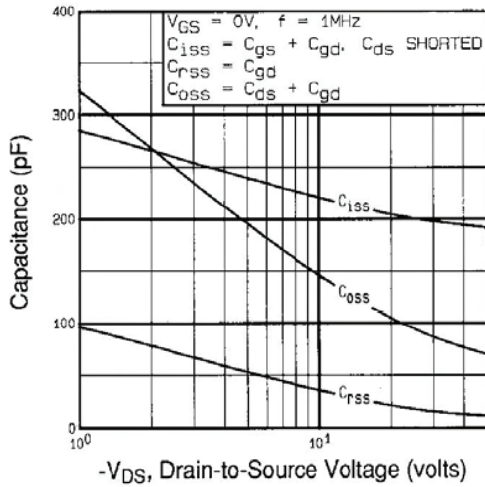


Fig. 4 - Typical Capacitance vs. Drain-to-Source Voltage

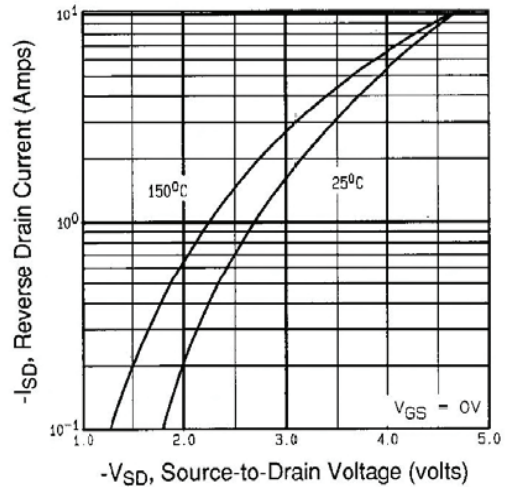


Fig. 6 - Typical Source-Drain Diode Forward Voltage

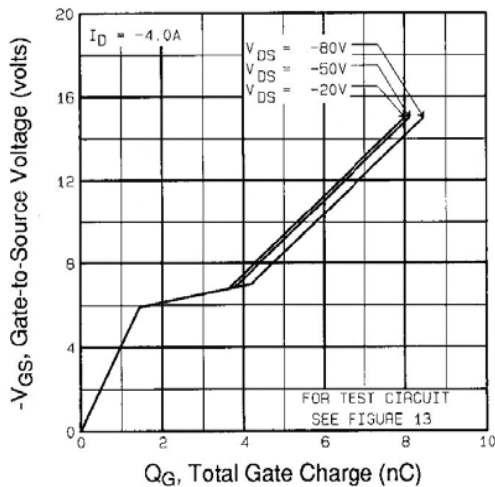


Fig. 5 - Typical Gate Charge vs. Gate-to-Source Voltage

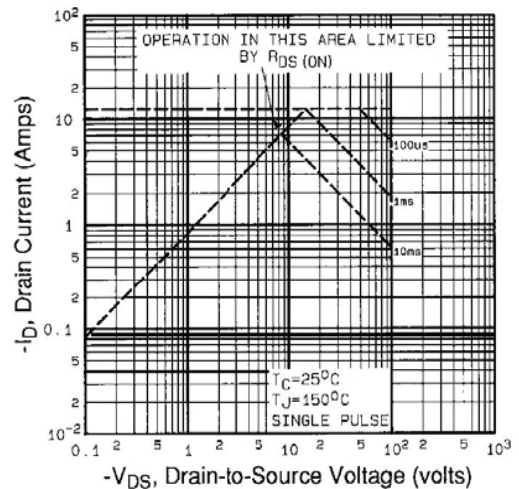


Fig. 7 - Maximum Safe Operating Area

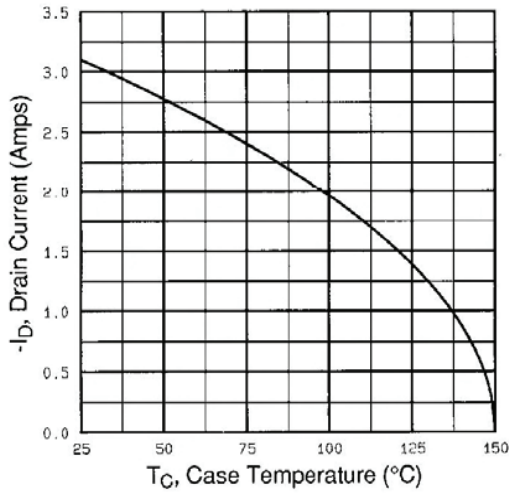


Fig. 8 - Maximum Drain Current vs. Case Temperature

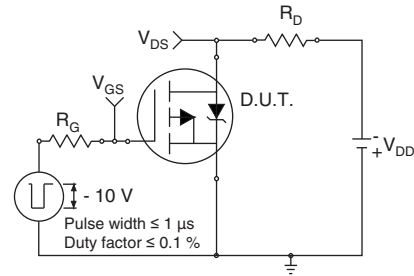


Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms

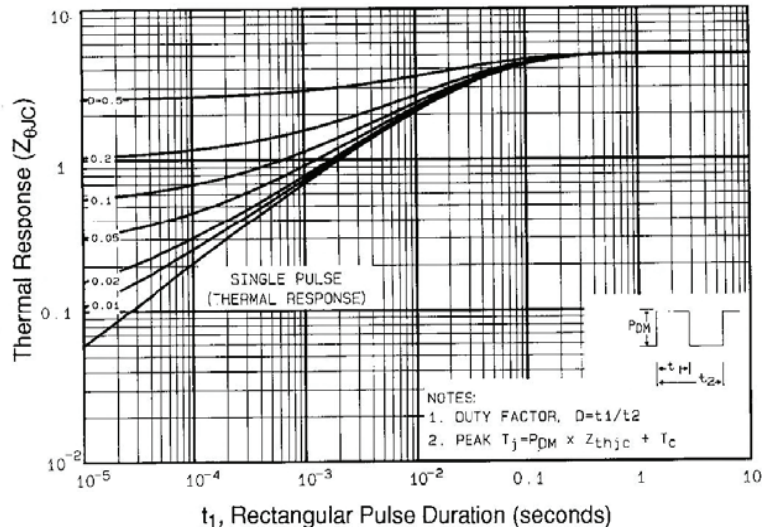


Fig. 9 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

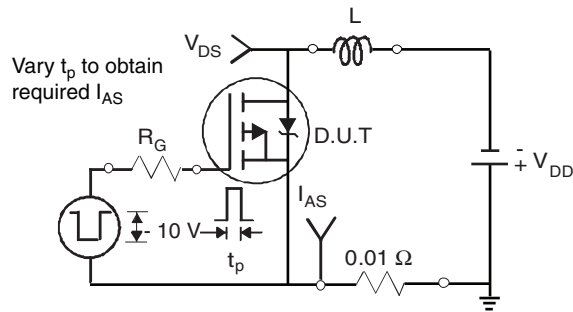


Fig. 12a - Unclamped Inductive Test Circuit

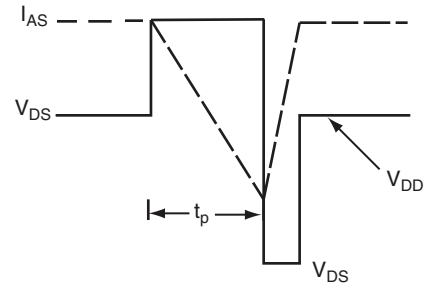


Fig. 12b - Unclamped Inductive Waveforms

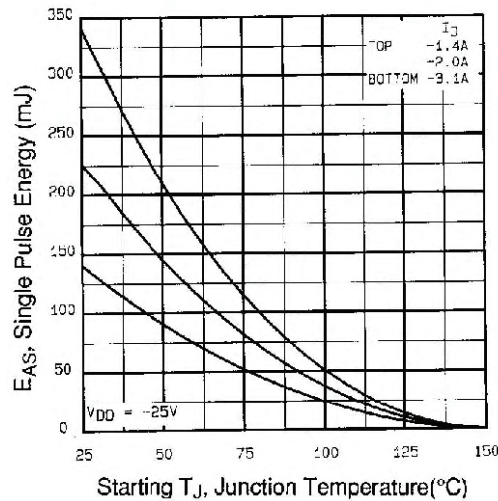


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

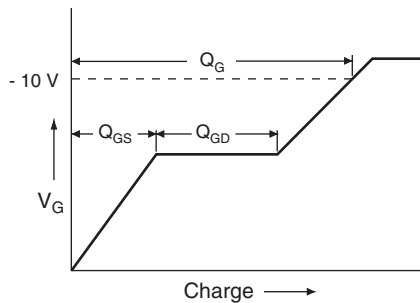


Fig. 13a - Basic Gate Charge Waveform

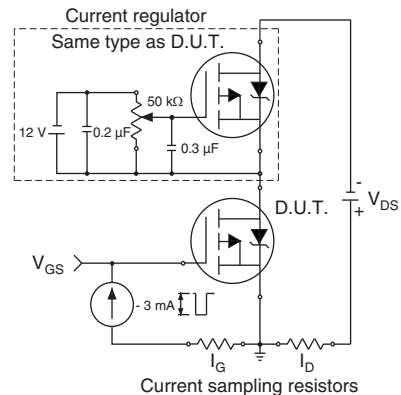
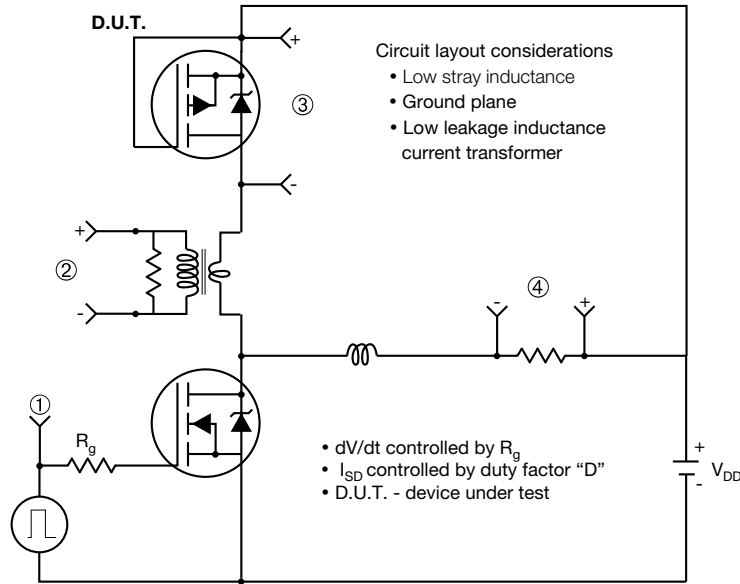


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

- Compliment N-Channel of D.U.T. for driver



Note

a. $V_{GS} = -5\text{ V}$ for logic level and -3 V drive devices

Fig. 10 - For P-Channel

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TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y



DIM.	MILLIMETERS	
	MIN.	MAX.
A	2.18	2.38
A1	-	0.127
b	0.64	0.88
b2	0.76	1.14
b3	4.95	5.46
C	0.46	0.61
C2	0.46	0.89
D	5.97	6.22
D1	4.10	-
E	6.35	6.73
E1	4.32	-
H	9.40	10.41
e	2.28 BSC	
e1	4.56 BSC	
L	1.40	1.78
L3	0.89	1.27
L4	-	1.02
L5	1.01	1.52

Note

- Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



MILLIMETERS		
DIM.	MIN.	MAX.
A	2.18	2.39
A1	-	0.13
b	0.65	0.89
b1	0.64	0.79
b2	0.76	1.13
b3	4.95	5.46
c	0.46	0.61
c1	0.41	0.56
c2	0.46	0.60
D	5.97	6.22
D1	5.21	-
E	6.35	6.73
E1	4.32	-
e	2.29 BSC	
H	9.94	10.34

MILLIMETERS		
DIM.	MIN.	MAX.
L	1.50	1.78
L1	2.74 ref.	
L2	0.51 BSC	
L3	0.89	1.27
L4	-	1.02
L5	1.14	1.49
L6	0.65	0.85
θ	0°	10°
θ1	0°	15°
θ2	25°	35°

Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022
 DWG: 5347

Case Outline for TO-251AA (High Voltage)

OPTION 1:



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	0.89	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b1	0.65	0.79	0.026	0.031
b2	0.76	1.14	0.030	0.045
b3	0.76	1.04	0.030	0.041
b4	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c1	0.41	0.56	0.016	0.022
c2	0.46	0.86	0.018	0.034
D	5.97	6.22	0.235	0.245

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
e	2.29 BSC		2.29 BSC	
L	8.89	9.65	0.350	0.380
L1	1.91	2.29	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.14	1.52	0.045	0.060
θ1	0°	15°	0°	15°
θ2	25°	35°	25°	35°

ECN: E21-0682-Rev. C, 27-Dec-2021
DWG: 5968

Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- Dimension are shown in inches and millimeters
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.13 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- Thermal pad contour optional with dimensions b4, L2, E1 and D1
- Lead dimension uncontrolled in L3
- Dimension b1, b3 and c1 apply to base metal only
- Outline conforms to JEDEC® outline TO-251AA



OPTION 2: FACILITY CODE = N



DIM.	MIN.	NOM.	MAX.
A	2.180	2.285	2.390
A1	0.890	1.015	1.140
b	0.640	0.765	0.890
b1	0.640	0.715	0.790
b2	0.760	0.950	1.140
b3	0.760	0.900	1.040
b4	4.950	5.205	5.460
c	0.460	-	0.610
c1	0.410	-	0.560
c2	0.460	-	0.610
D	5.970	6.095	6.220
D1	4.300	-	-

DIM.	MIN.	NOM.	MAX.
D2	5.380	-	-
E	6.350	6.540	6.730
E1	4.32	-	-
e	2.29 BSC		
L	8.890	9.270	9.650
L1	1.910	2.100	2.290
L2	0.890	1.080	1.270
L3	1.140	1.330	1.520
L4	1.300	1.400	1.500
theta1	0°	7.5°	15°
theta2	4°	-	-

ECN: E21-0682-Rev. C, 27-Dec-2021
DWG: 5968

Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- All dimension are in millimeters, angles are in degrees
- Heat sink side flash is max. 0.8 mm

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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